

Features

- Uses PingWei advanced PerfectMOS2 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Qualified according to AEC-Q101 criteria

Benefits

- High robustness and reliability
- Direct heatsink on TOP plate
- Low power loss, high power density
- PCB Area Saving

Applications

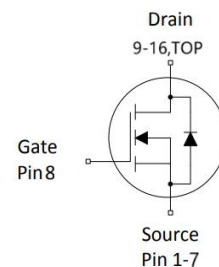
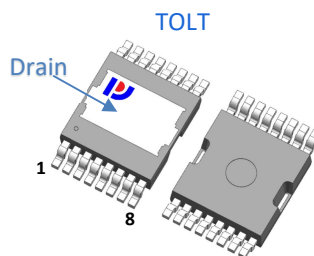
- General automotive applications
- High power density applications



100% DVDS Tested
100% Avalanche Tested

Product Summary

V_{DS}	100V
$R_{DS(on)}@10V$ typ	1.3mΩ
$I_D(\text{Silicon})$	342A



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
PW016N10LTSQ	PW016N10LTSQ	TOLT	Tape&Reel	13 inches	24mm	1000

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	100	V
Continuous drain current	I_D	342	A
$T_C = 25^\circ\text{C}$ (Silicon limit)		300	
$T_C = 25^\circ\text{C}$ (Package limit)		242	
$T_C = 100^\circ\text{C}$ (Silicon limit)		35	
$T_a = 25^\circ\text{C}$ (See RthJA)			
Pulsed drain current ($T_C = 25^\circ\text{C}$)	$I_{D \text{ pulse}}$	1200	A
Avalanche energy, single pulse ($L=0.5\text{mH}$, $V_{ds}=50\text{V}$)	E_{AS}	484	mJ
Gate-Source voltage	V_{GS}	± 20	V
Power dissipation	P_{tot}	385	W
$T_C = 25^\circ\text{C}$		4.1	
$T_a = 25^\circ\text{C}$ (See RthJA)			
Operating junction and storage temperature	T_j, T_{stg}	-55...+175	$^\circ\text{C}$
Reflow soldering temperature (10s)	T_{sold}	260	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	RthJC	-	-	0.39	°C/W	-
Thermal resistance, junction - ambient	RthJA	-	37	-	°C/W	1 inch ² , 2oz single copper FR-4 PCB

Electrical Characteristic (at T_j = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV _{DSS}	100	-	-	V	V _{GS} =0V, I _D =250uA
Gate threshold voltage	V _{GS(th)}	2.5	-	3.5	V	V _{DS} =V _{GS} , I _D =250uA
Zero gate voltage drain current	I _{DSS}	-	-	1	μA	V _{DS} =100V, V _{GS} =0V T _j =25°C T _j =150°C
Gate-source leakage current	I _{GSS}	-	±10	±100	nA	V _{GS} =±20V, V _{DS} =0V
Drain-source on-state resistance	R _{DS(on)}	-	1.3	1.6	mΩ	V _{GS} =10V, I _D =50A
Transconductance	g _{fs}	-	140	-	S	V _{DS} =5V, I _D =50A

Dynamic Characteristic

Input Capacitance	C _{iss}	-	12768	-	pF	V _{GS} =0V, V _{DS} =50V, f=100KHz
Output Capacitance	C _{oss}	-	3662	-		
Reverse Transfer Capacitance	C _{rss}	-	42	-		
Gate Total Charge	Q _G	-	166	-	nC	V _{DS} =50V, I _D =100A , V _{GS} =10V
Gate-Source charge	Q _{gs}	-	67	-		
Gate-Drain charge	Q _{gd}	-	20	-		
Turn-on delay time	t _{d(on)}	-	40	-	ns	V _{GS} =10V, V _{DD} =50V, R _{G_ext} =1.6Ω, I _D =25A
Rise time	t _r	-	53	-		
Turn-off delay time	t _{d(off)}	-	87	-		
Fall time	t _f	-	17	-		
Gate resistance	R _G	-	1.1	-	Ω	V _{GS} =0V, V _{DS} =0V, f=1MHz

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.8	1.2	V	$V_{GS}=0V, I_{SD}=50A$
Body Diode Continuous Forward Current	I_S	-	-	300	A	TC = 25°C
Body Diode Pulsed Current	I_S pulse	-	-	1200	A	TC = 25°C
Body Diode Reverse Recovery Time	t_{rr}	-	109	-	ns	$V_R=50V, I_F=50A,$ $diF/dt=100A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}	-	345	-	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

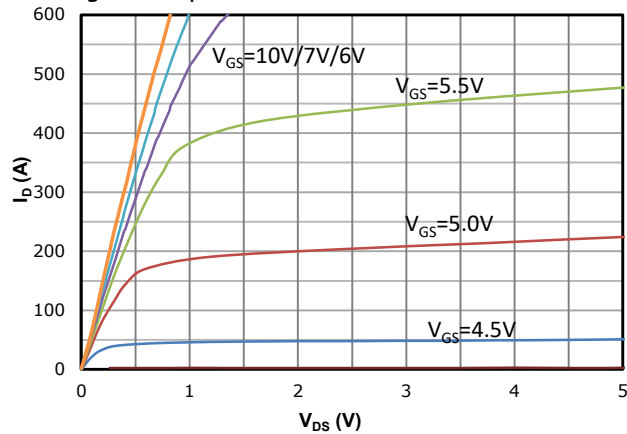


Fig 2: Transfer Characteristics

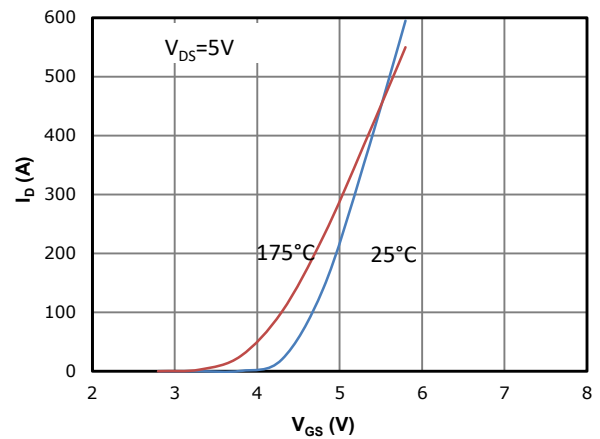


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

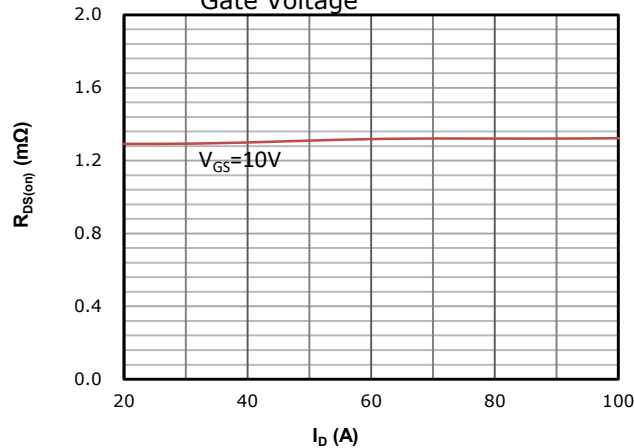


Fig 4: $R_{DS(on)}$ vs Gate Voltage

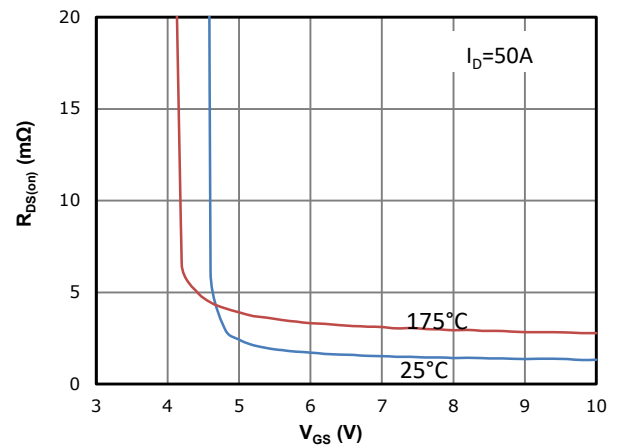


Fig 5: $R_{DS(on)}$ vs. Temperature

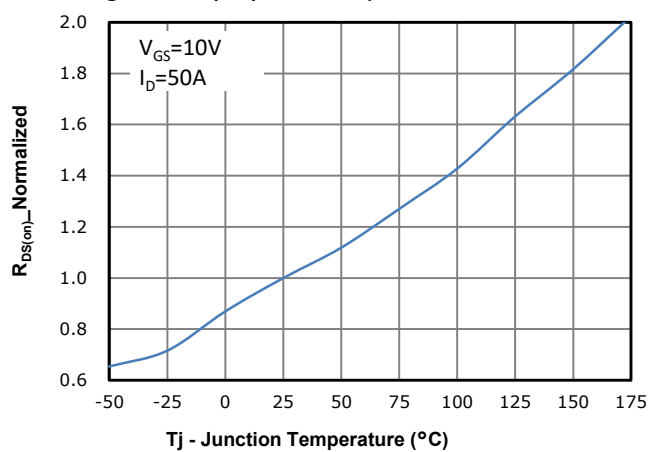


Fig 6: $V_{GS(th)}$ vs. Temperature

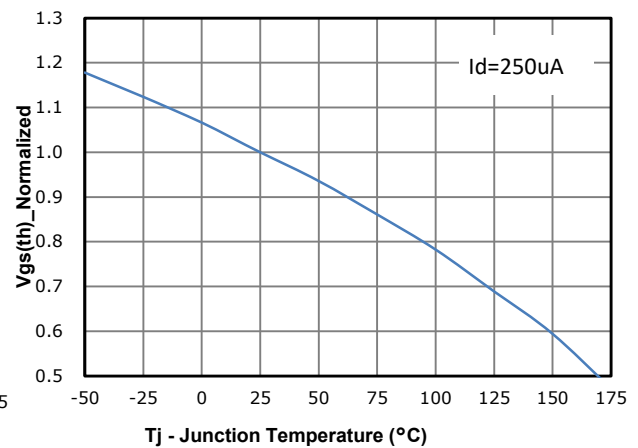


Fig 7: BVdss vs. Temperature

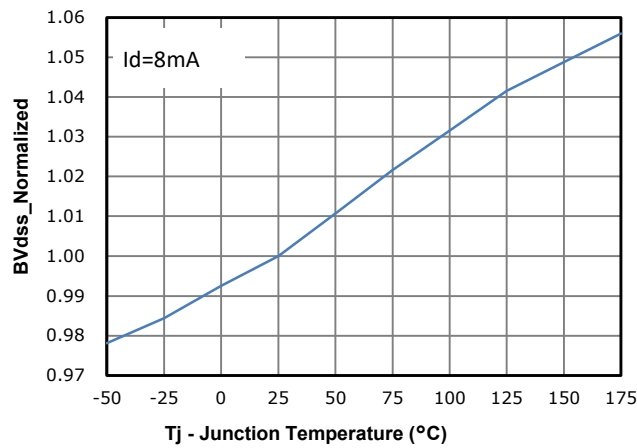


Fig 8: Capacitance Characteristics

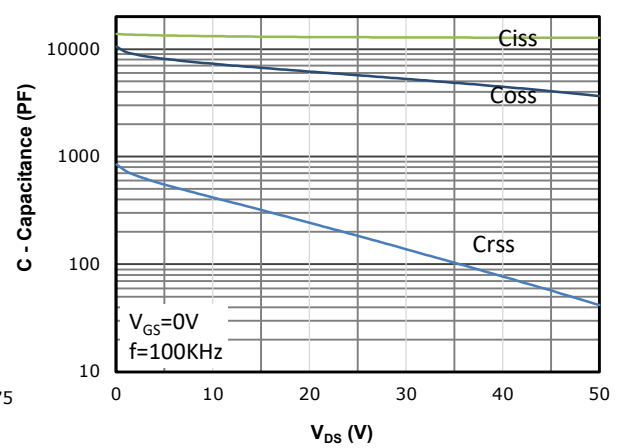


Fig 9: Gate Charge Characteristics

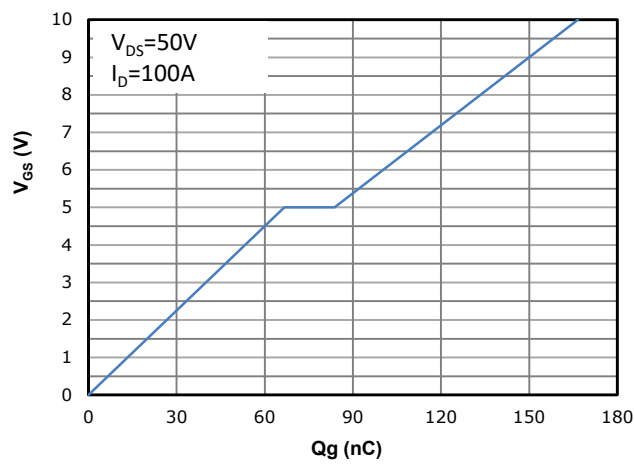


Fig 10: Body-diode Forward Characteristics

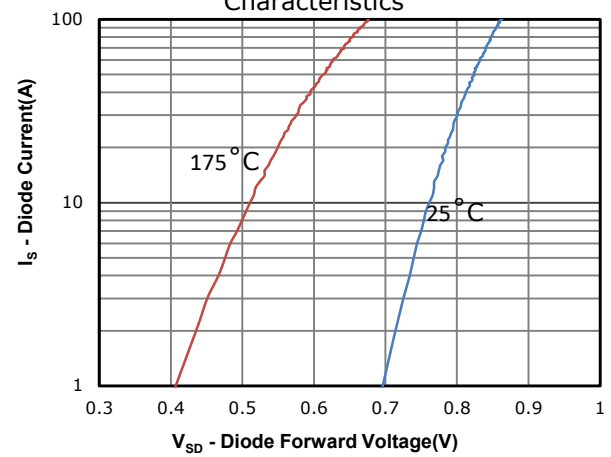


Fig 11: Power Dissipation

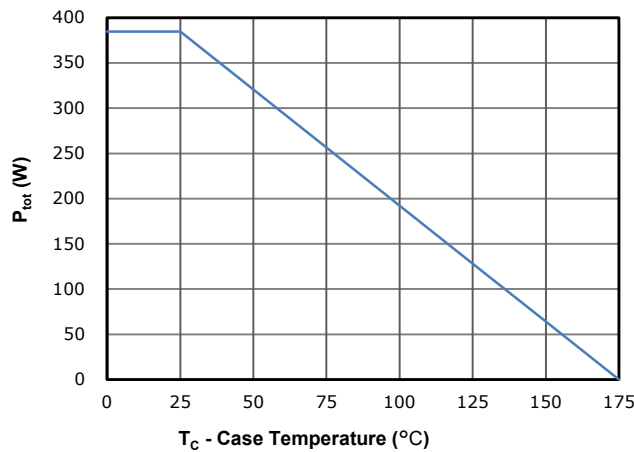


Fig 12: Drain Current Derating

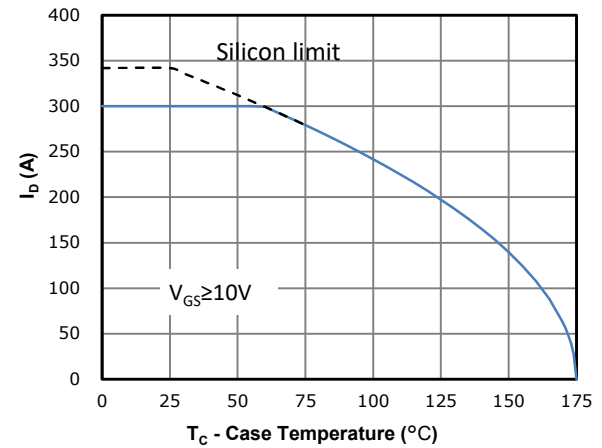


Fig 13: Safe Operating Area

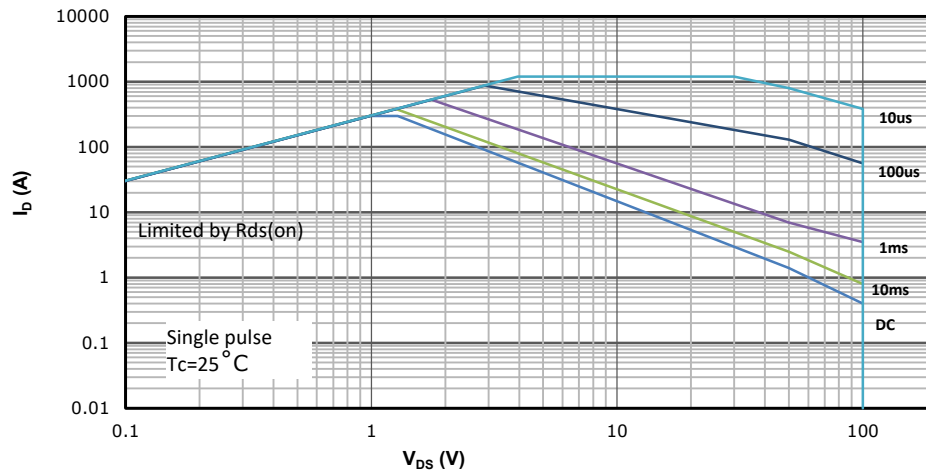
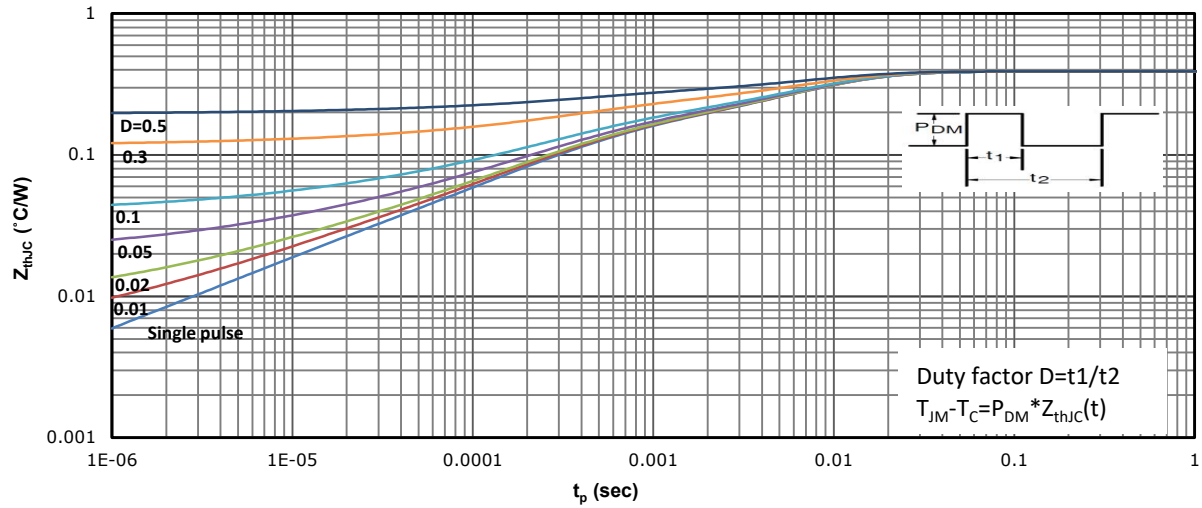
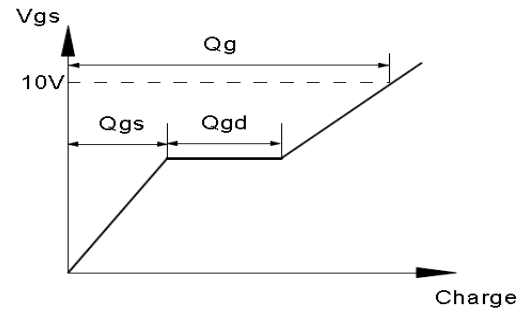
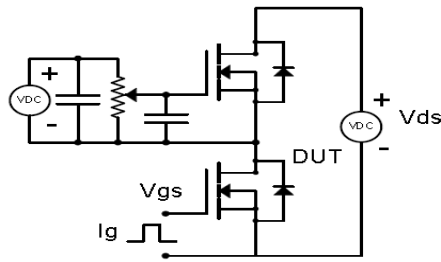


Fig 14: Max. Transient Thermal Impedance

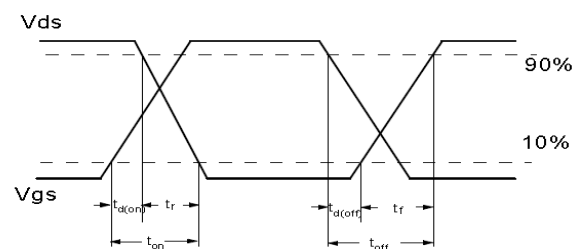
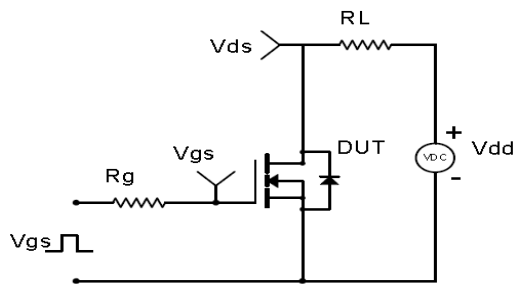


Test Circuit & Waveform

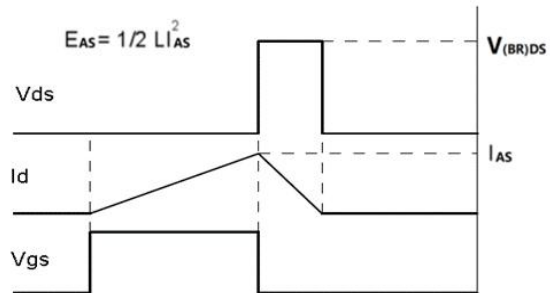
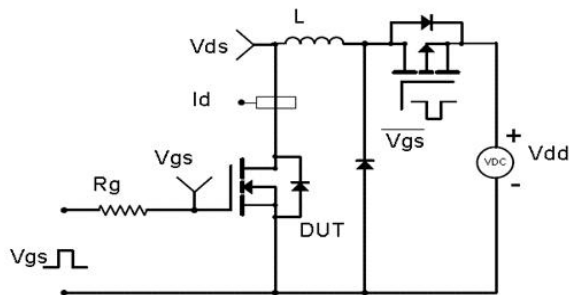
Gate Charge Test Circuit & Waveform



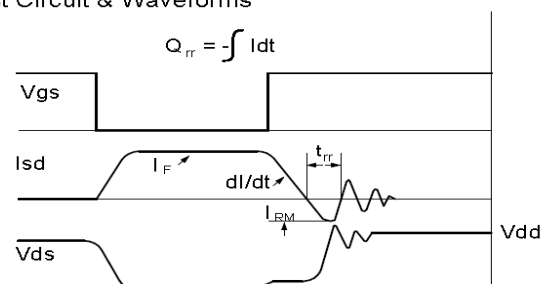
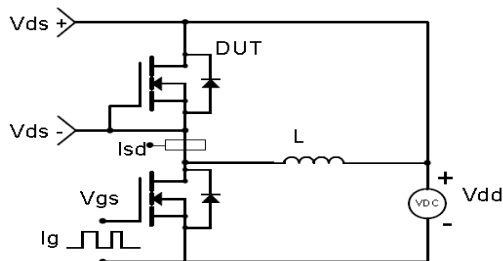
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Revision History

Revision	Date	Major changes
1.0	2025/6/12	Release of Formal Version
1.1	2025/8/5	Update Pakage Outline&Trr/Qrr

Disclaimer

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

The product is not intended for use in applications that require extraordinary levels of quality and reliability, such as aviation/aerospace and life-support devices or systems.

Buyer is responsible for its products and applications using PingWei products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by PingWei.

"Typical" parameters which may be provided in PingWei data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts

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